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[54] **IMPLANTATION AND ELECTRICAL ACTIVATION OF DOPANTS INTO MONOCRYSTALLINE SILICON CARBIDE**

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Related U.S. Application Data

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[52] **U.S. Cl.** **437/22**; 437/25; 437/100

[58] **Field of Search** 437/22, 25, 100; 148/DIG. 148

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[57] **ABSTRACT**

The invention is a method of ion implantation of dopant ions into a substrate of silicon carbide. In the method, the implantation takes place at elevated temperatures, following which the substrate may be oxidized or annealed.

24 Claims, 1 Drawing Sheet